

L Number	Hits	Search Text	IB	Time stamp
1	12000	ESD (electrostatic near discharge)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/07 09:06
2	28634	SCR (silicon near control)S4 near rectifier)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/07 09:09
3	322624	triggerS4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/07 09:09
5	397	(ESD (electrostatic near discharge)) and (SCR (silicon near control)S4 near rectifier)) and triggerS4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/07 09:09

L Number	Hits	Search Text	DB	Time stamp
1	12000	ESD (electrostatic near discharge)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TIB	2002/05/07 09:16
2	25654	SCR (silicon near controll\$4 near rectifier)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TIB	2002/05/07 09:08
3	322624	trigger\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TIB	2002/05/07 09:09
5	397	(ESD (electrostatic near discharge (SCR (silicon near controll\$4 near rectifier)) and trigger\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TIB	2002/05/07 09:14
6	598	(ESD (electrostatic near discharge)) and (SCR (silicon near controll\$4 near rectifier))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TIB	2002/05/07 09:14